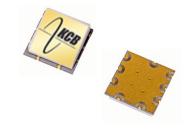
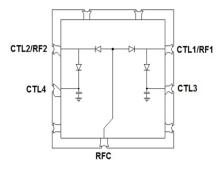
KS113-52 SPDT 50W SWITCH 0.02 – 2.0 GHZ





DESCRIPTION

The KS113-52 is a SPDT PIN switch that offers high power handling and low insertion loss in a compact surface mount package. Built on a highly thermally conductive Aluminum Nitride (AIN) substrate, this switch is ideal for high performance commercial and military applications where low loss combined with high adjacent port isolation is required. In addition, the thick copper under metal provides superior loss performance as well as higher bias current handling than traditional metallization schemes. High power diodes have been chosen to provide the optimum blend of loss, isolation and harmonic performance.

THE HIGHEST STANDARD IN

FEATURES

- ✓ High Power Series-Shunt PIN Diode Design
- ✓ Broadband operation from 0.02 2.0 GHz
- ✓ Surface Mount 7mm QFN-style Leadless Package
- ✓ Rugged Aluminum Nitride Carrier with Thick Copper Traces

APPLICATIONS

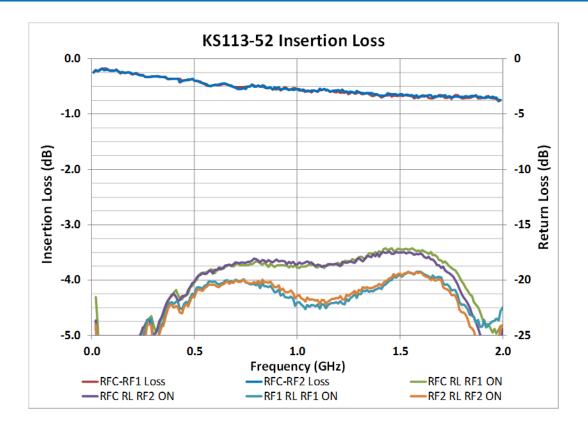
- ✓ Microwave Radios
- ✓ Military Radios
- VSAT
- ✓ **Telecom Infrastructure**
- ✓ Test Equipment

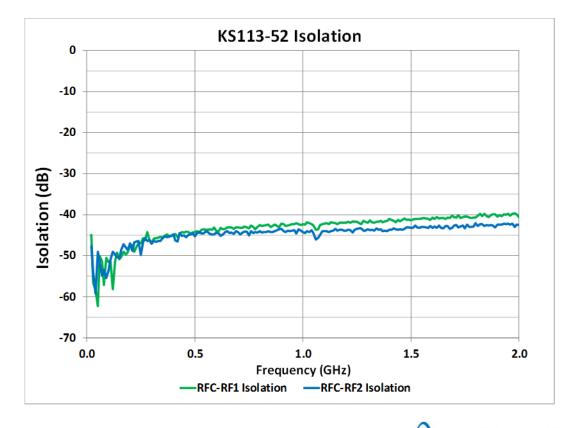
ELECTRICAL CHARACTERISTICS (+25°C)

Parameter	Conditions	Min	Typical	Max	Units
Insertion Loss	0.02 – 0.5 GHz 0.5 – 1.0 GHz 1.0 – 2.0 GHz		0.03 0.50 0.75	0.5 0.75 1.0	dB dB dB
Isolation	0.02 – 2.0 GHz		45		dB
Return Loss	0.02 – 0.5 GHz 0.5 – 1.0 GHz 1.0 – 2.0 GHz		20.8 17.7 17.7	17.7 15.6 15.6	dB dB dB

KS113-52 | SPDT 50W SWITCH.02 - 2 GHZ

'YPICAL PERFORMANCE (+25°C)



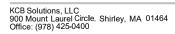


(CB <mark>SOL</mark>

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info@kcbsolutions.com

www.kcbsolutions.com KS113-52DS Rev (-1)



KS113-52 | SPDT 50W SWITCH .02 – 2 GHZ

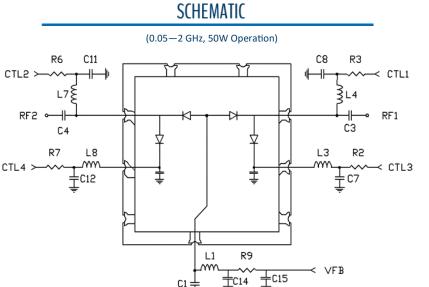
TRUTH TABLE/CONTROL VOLTAGES

ICTL = 20mA - 100mA , VCTL = 25V-100V)

CTL1	CTL2	CTL3	CTL4	RFC-RF1	RFC-RF2
-I _{CTL}	+V _{RB}	+V _{RB}	-I _{CTL}	Low Loss	Isolation
+V _{RB}	-I _{CTL}	-I _{CTL}	+V _{RB}	Isolation	Low Loss

Truth Table Notes:

- 1. ICTL = 20mA 100mA bias current is recommended for low loss performance.
- 3. VRB must be greater than the worst case RF voltage excursion to maintain a reverse bias on the series diode.



RFC

C1

±C14

Location	Value	Part Number	Manufacturer
C1,C3,C4	1000pF, 250V	C1608NP02E102J080AA	ТDК
C14,C15,C7,C8,C11,C12	47pF, 250V	600S470JT250XT	ATC
R9,R3,R6	22 Ohms, 1/4W	ERJ-PA3F22R0V	Panasonic
R7,R2	4.7K Ohms, 3W	35224K7JT	TE Connectivity
L1,L3,L4,L7,L8	180 nH	0603HP-R18XGLW	Coilcraft

APPLICATION TRUTH TABLE/ CONTROL VOLTAGES

(VRB = +100V, ICTL = 50 mA, VFB = +3.3V)

CTL1	CTL2	CTL3	CTL4	RFC-RF1	RFC-RF2
0V	+100V	+100V	0V	Loss	Isolation
+100V	0V	0V	+100V	Isolation	Loss



Electrostatic Sensitive Device. Proper ESD precaution should be used when handling device.

Schematic Notes:

- 1. CTL1-CTL4 should be chosen to maintain reverse bias through peak RF voltage excursions during the OFF state and to maintain proper forward bias current (ICTL) during ON state. See truth table.
- 2. DC blocking capacitors on RF lines should be large enough to provide low loss at the lowest operating frequency.
- 3. All inductors should be large enough to provide high impedances at the lowest operating frequency.
- 4. Bypass capacitors should be large enough to adequately filter supply noise from DC control lines.



KS113-52 | SPDT 50W SWITCH.02 – 2 GHZ

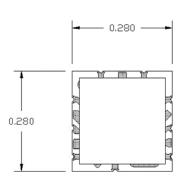
ABSOLUTE MAXIMUM RATINGS

-250	+250	Volts
	50	W ⁽¹⁾
-55	+150	°C
-55	+85	°C
	200	mA
0.02	2.0	GHz
	-55	-55 +150 -55 +85 200 -

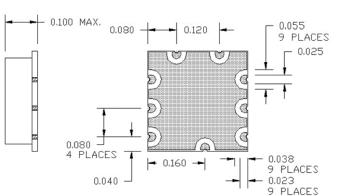
Notes:

 Max Base Plate Temp =+85°C. For temperatures above +85°C derate linearly to +150°C using P_{max} = 115.38 - 0.769*T_{amb}

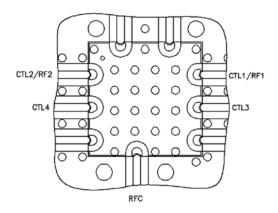
OUTLINE DRAWING



Dimensions are shown in inches.



RECOMMENDED SOLDER LAYOUT



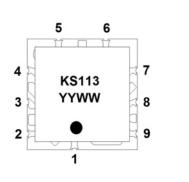
Notes:

- 1. Maximum reflow temperature: 265°C
- 2. Ground all unused ports.
- 3. Trace widths for Rogers© RO4003C material with 0.008" ground plane spacing.
- 4. DXF file available upon request.
- 5. Contact KCB Solutions for further guidance on device placement and attachment.



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PINOUT



1	RFC
2	GND
3	CTL4
4	RF2/CTL2
5	GND
6	GND
7	RF1/CTL1
8	CTL3
9	GND